06.25-04

Express Mail No. EU687958457U Attorney Docket No.: AM-9230

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

RE APPLICATION OF: Soo Young Choi et al.

§ GROUP ART UNIT: Unknown

SERIAL NO.: 10/829,016

Unknown

FILED: April 30, 2004

EXAMINER:

FOR: CONTROLLING THE PROPERTIES AND

UNIFORMITY OF A SILICON NITRIDE FILM

BY CONTROLLING THE FILM FORMING PRECURSORS

Attorney Docket No.:

AM-9230

Date: June 23, 2004

INFORMATION DISCLOSURE STATEMENT TRANSMITTAL LETTER

Hon. Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

Applicants are submitting the subject Information Disclosure Statement under 37 CFR § 1.97(b)(1). This Information Disclosure Statement is being submitted within three (3) months of the filing date of the subject application.

CERTIFICATE OF MAILING UNDER 37 CFR § 1.10

I hereby certify that this paper is being deposited with the U.S. Postal Service on the date shown below with sufficient postage as U.S. EXPRESS MAIL NO. EU687958457US in an envelope addressed to: Mail Stop DD, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Date: June 23, 2004

Shirley L. Church, Reg. No. 31,858

Applicants do not believe that any fee is due in connection with the filing of this Information Disclosure Statement under 37 CFR § 1.97(b)(1). However, in the event that any additional fee is due, the Commissioner is hereby authorized to charge Deposit Account No. 50-1512 of Shirley L. Church, Sunnyvale, California, in the amount of such fee.

This transmittal letter is submitted in duplicate for accounting purposes.

Respectfully submitted,

Shirley L. Church
Shirley L. Church

Registration No. 31,858 Attorney for Applicants

Correspondence Address:
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Applied Materials, Inc.
P.O. Box 450-A
Santa Clara, California 95052



Express Mail No. EU687958447US Attorney Docket No.: AM-9230

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Soo Young Choi et al.

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INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(b)(1)

Hon. Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

In accordance with 37 CFR § 1.97(b)(1), applicants hereby request consideration of this Information Disclosure Statement. This Information Disclosure Statement is being submitted within three (3) months of the filing date of the subject application. Applicants are providing herewith a copy of each document cited on the attached Form PTO-1449.

CERTIFICATE OF MAILING UNDER 37 CFR § 1.10

I hereby certify that this paper is being deposited with the U.S. Postal Service on the date shown below with sufficient postage as U.S. EXPRESS MAIL NO. EU687958457US in an envelope addressed to: Mail Stop DD, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

Date: June 23, 2004

Shirley L. Church, Reg. No. 31,858

The submission of this Information Disclosure Statement and Form PTO-1449 is not an admission that the art cited is "prior art" with respect to the present invention, nor is it a representation that no better art exists. Applicants hereby reserve the right to swear behind or otherwise disprove any alleged "prior" nature of any art cited should the facts support and the situation warrant such an action.

If the Examiner has any questions, s/he is respectfully requested to contact the undersigned attorney at the telephone number set forth below.

Respectfully submitted,

Shirley L/Church

Registration No. 31,858 Attorney for Applicants

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Correspondence Address:
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FORM PE Requive

FORM PTO-1449 (Equivalent) U.S. Department of Commerce Patent and Trademark Office

U.S. Application Serial No. 10/829,016 Atty. Docket No.
AM-9230

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use several sheets if necessary)

Soo Young Choi et al. Applicants

April 30, 2004 Filing Date

<u>Unknown</u> Group

U. S. PATENT DOCUMENTS						
Examiner Initial	Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate
	5,399,387	03/21/95	Law et al.	427	574	
·	5,928,732	07/27/99	Law et al.	427	579	
		U. S.	PATENT APPLICATI	ON DOCUMEN	TS	
Examiner	Document		blication			
<u>Initial</u>	Number		Date Name	<u>Clas</u>	<u>ss Sub</u>	class Filing Dat
						_
	2002/014687	79 10	/10/02 Fu et al.	438	230	12/21/01
	2002/014687	Publicatio	/10/02 Fu et al. FOREIGN PATENT D	OCUMENTS		Translation
Examiner Initial	2002/014687		/10/02 Fu et al. FOREIGN PATENT D		230 Subclass	
Examiner Initial	2002/014687	Publicatio Date	/10/02 Fu et al. FOREIGN PATENT D	OCUMENTS		Translation

	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)
	S. K. Kim et al., "A Novel Self-Aligned Coplanar Amorphous Silicon Thin Film Transistor", ISSN0098-0966X/98/2901 (1998).
	L. Kyung-ha, "A Study on Laser Annealed Polycrystalline Silicon Thin Film Transistors (TFTs) with SiNx Gate Insulator", Kyung Hee University, Ch. 2 & 4 (1998).
	Y. Park, "Bulk and interface properties of low-temperature silicon nitride films deposited by remote plasma enhanced chemical vapor deposition", Journal of Materials Science: Materials in Electronics, Vol. 12, pp. 515 - 522 (2001).
	A. Sazonov et al., "Low Temperature a-Si:H TFT on Plastic Films: Materials and Fabrication Aspects", Proc. 23 rd International Conference on Microelectronics (MIEL 2002), Vol. 2, Niš, Yugoslavia (May 2002).
	D. B. Thomasson et al., "High Mobility Tri-Layer a-Si:H Thin Film Transistors with Ultra-Thin Active Layer", 1997 Society for Information Display International Symposium Digest of Technical Papers, Vol. 28, pp. 176 - 179 (May 1997).
Examiner	Date Considered

Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.